NSN 5962-01-370-2025

Memory Microcircuit - Page 1 of 2



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Body Length: 1.280 inches Body Widh: Between 0.220 inches and 0.310 inches Body Height: 0.185 inches Maximum Power Dissipation Rating: 1.02 watts Operating Tempurature Range: -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius Features Provided: Bipolar and wenable and programmed and 3-state output and monolithic Inclosure Material: Ceramic Inclosure Material: Ceramic Inclosure Configuration: Dual-inline Output Logic Form: 14 input Case Outline Source And Designator: D-9 mili-maget0 Current Rating Per Characteristic: 185.00 miliamapers reverse current, dc absolute Terminal Surface Treatment: Solder Voltage Rating And Type Per Characteristic: 0.05 input picofarads and 14.00 output picofarads Chaiten Rating Per Characteristic: 0.05 input picofarads and 14.00 output picofarads Output picofarads and 14.00 output picofarads Chaiten Rating Per Characteri
Bedy Width: Between 0.220 inches and 0.310 inches Bedy Height: 0.165 inches Maximum Power Dissipation Rating: 1.02 watts Operating Tempurature Range: -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+125.0 degrees celsius Fatures Provided: Bipolar and wich able and programmed and 3-state output and monolithic Inclosure Material: Ceramic Paul-in-line Ouget Logic Form: Transistor transistor logic Input Crock Pateres 14 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 18:00 milliamperes reverse current, dc absolute Caramic Vidage Rating And Type Per Characteristic: 0.5 volts power source and 7.0 volts power source Characteristic: 0.5 volts power source and 7.0 volts power source Characteristic: 0.5 volts power source and 7.0 volts power source Case Outline Source And Dosignator: 0.5 volts power source and 7.0 volts power source Casting Per Characteristic:
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65.00 nanoseconds access Memory Device Type: Prom
Memory Device Type: Prom
Prom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:
N/a

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Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

